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[Vishay/Siliconix](#)
[SI4484EY-T1-E3](#)

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sales@integrated-circuit.com



Si4484EY
 Vishay Siliconix

N-Channel 100-V (D-S) MOSFET

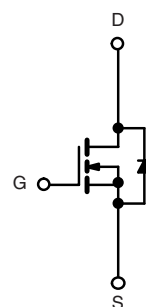
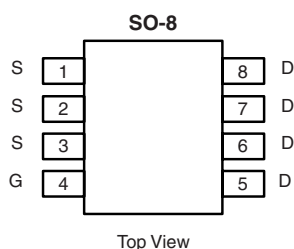
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
100	0.034 at $V_{GS} = 10$ V	6.9
	0.040 at $V_{GS} = 6.0$ V	6.4

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- 175 °C Maximum Junction Temperature
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC



RoHS
 COMPLIANT
 HALOGEN
FREE
 Available



Ordering Information: Si4484EY-T1-E3 (Lead (Pb)-free)
 Si4484EY-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	100		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 175$ °C) ^a	I_D	$T_A = 25$ °C	6.9	4.8	A
		$T_A = 85$ °C	5.4	3.7	
Pulsed Drain Current	I_{DM}	30		mJ	
Avalanche Current	I_{AR}	25			
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	E_{AR}	31		A	
Continuous Source Current (Diode Conduction) ^a	I_S	3.1	1.5		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	3.8	1.8	W
		$T_A = 85$ °C	2.3	1.1	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	33	40	°C/W
		Steady State	70	85	
Maximum Junction-to-Foot (Drain)	R_{thJF}	17	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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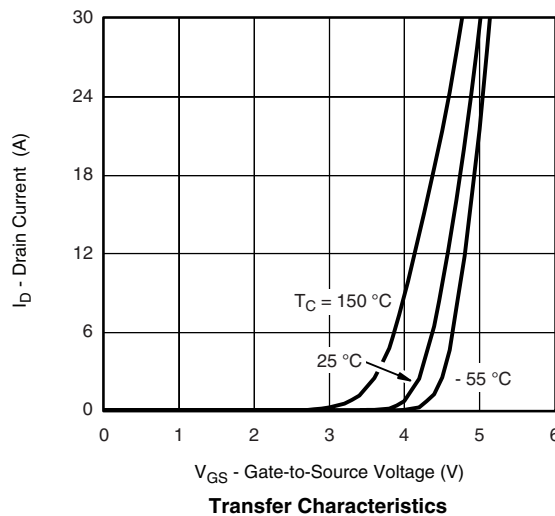
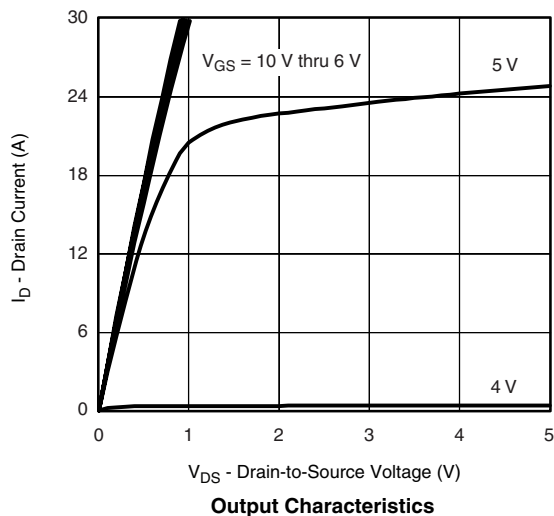
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			20	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.9\text{ A}$		0.028	0.034	Ω
		$V_{GS} = 6.0\text{ V}, I_D = 6.4\text{ A}$		0.032	0.040	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 6.9\text{ A}$		25		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.1\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 6.9\text{ A}$		24	30	nC
Gate-Source Charge	Q_{gs}			7.6		
Gate-Drain Charge	Q_{gd}			5.4		
Gate Resistance	R_g		0.5	1.25	2.2	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 50\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		16	30	ns
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			35	70	
Fall Time	t_f			20	40	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 3.1\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		50	80	

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

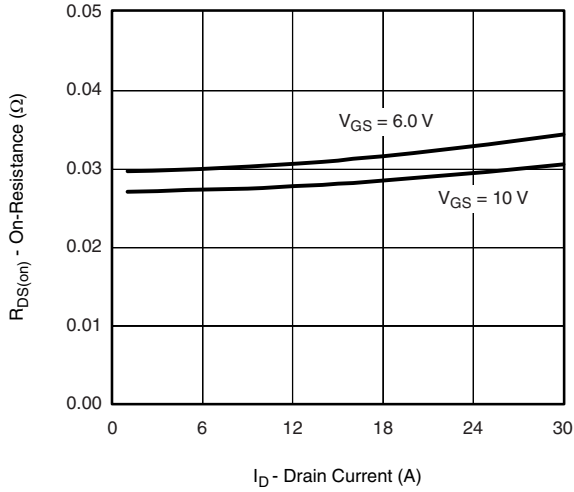
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



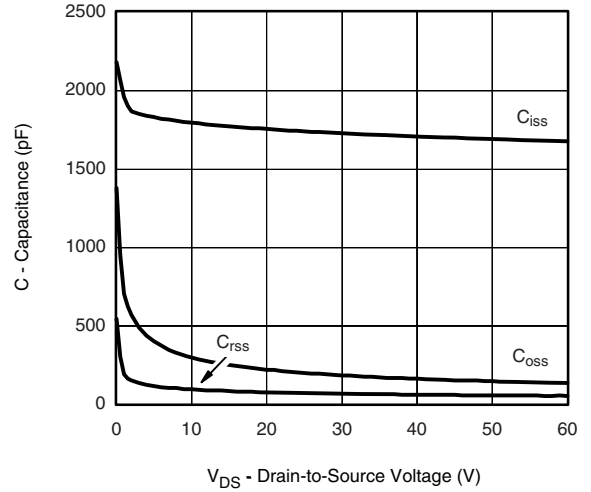


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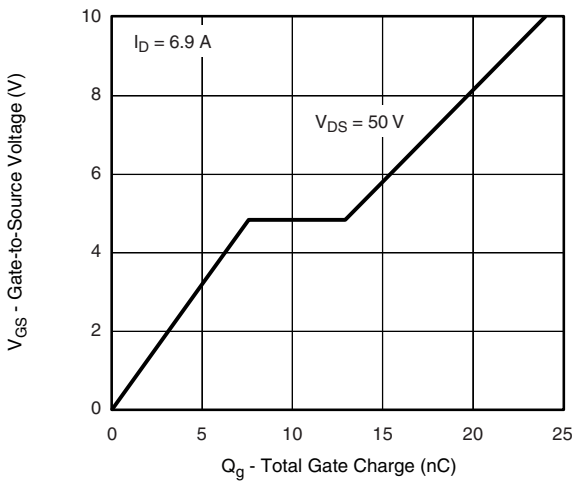
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



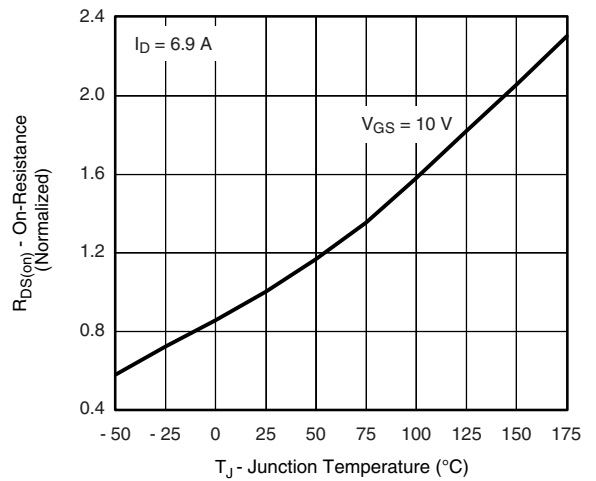
On-Resistance vs. Drain Current



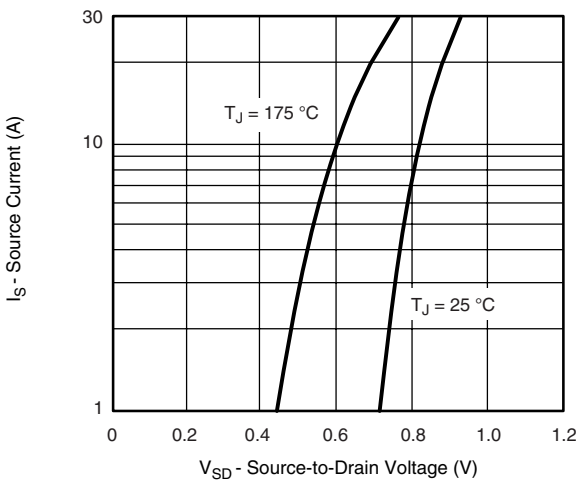
Capacitance



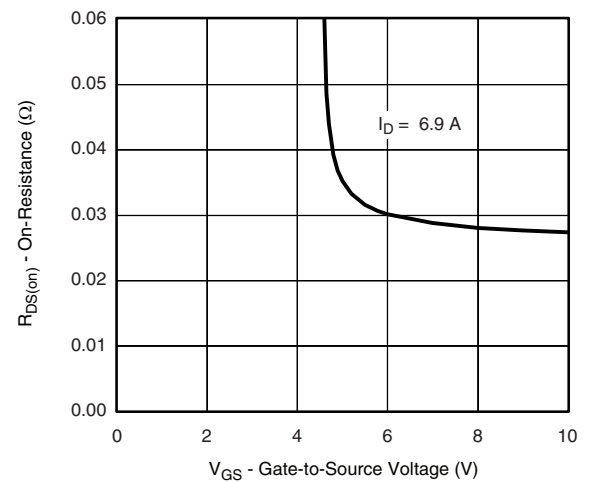
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

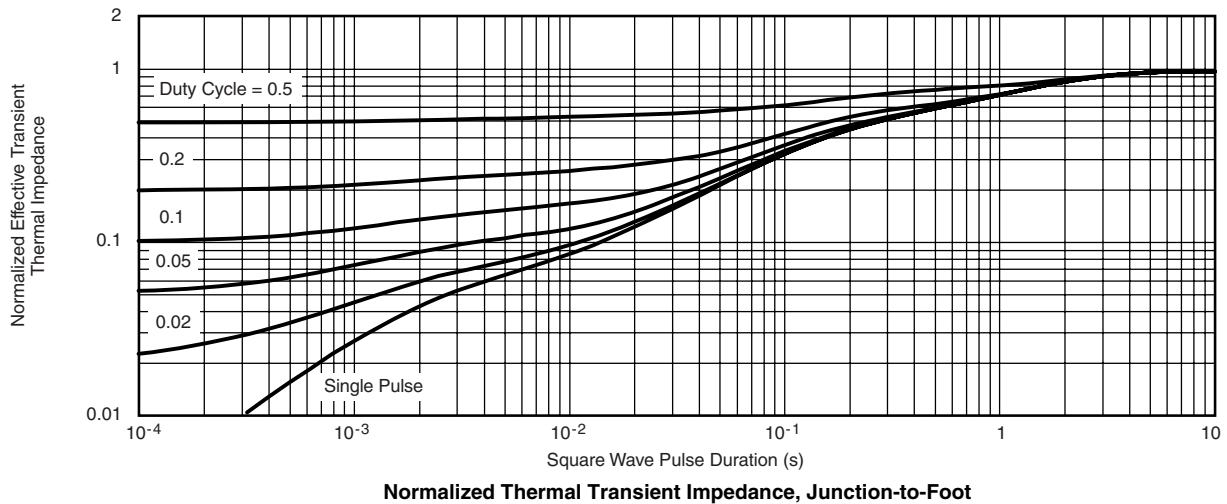
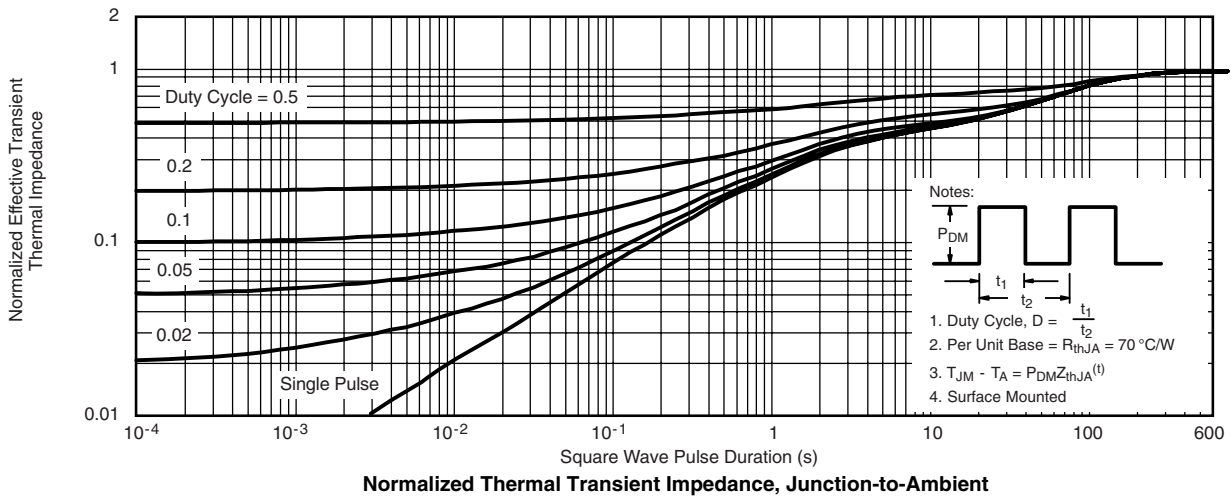
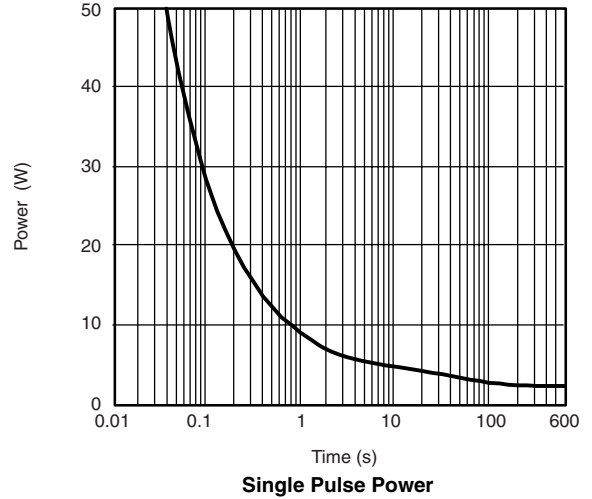
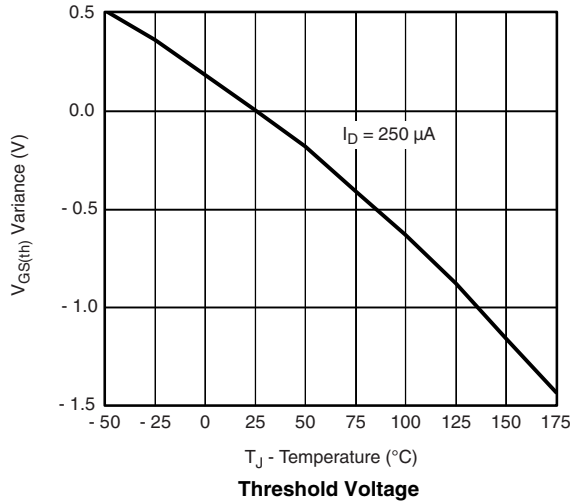


On-Resistance vs. Gate-to-Source Voltage

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppq?71189.

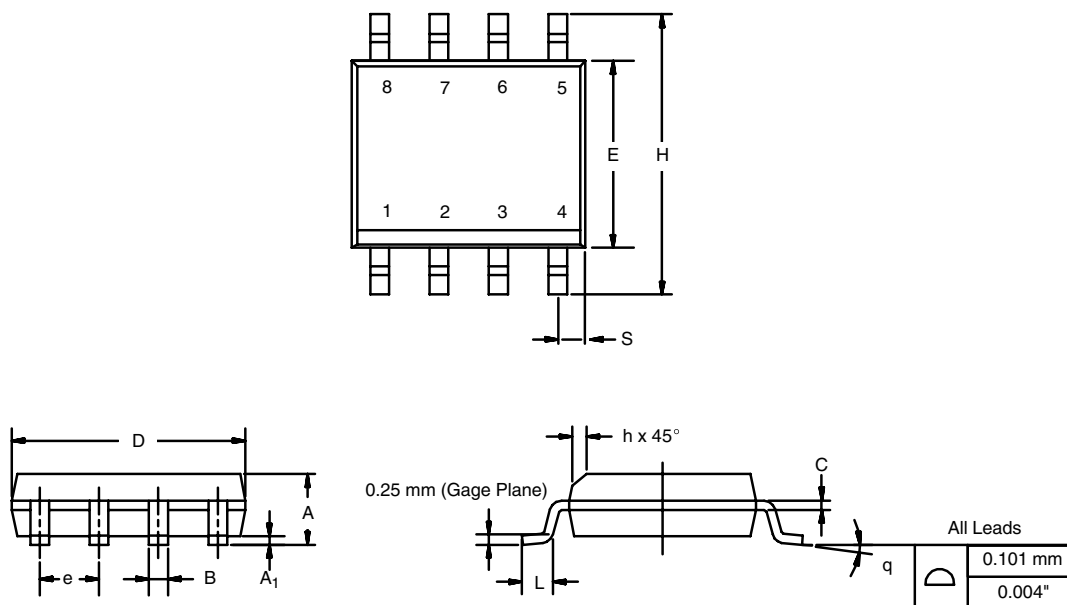


Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026

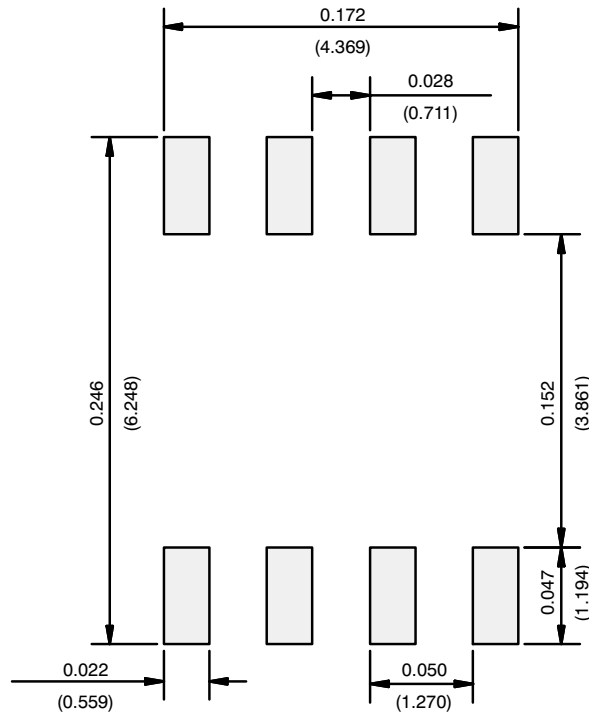
ECN: C-06527-Rev. I, 11-Sep-06
DWG: 5498

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
 Dimensions in Inches/(mm)

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